

IN THE CLAIMS

Claim 1 (Canceled)

2. (Currently Amended) An information storage medium which comprises a substrate and, stacked thereon in the following successive order, at least a first protective layer, a first interfacial layer ~~which is comprised of an oxide or a nitride~~, a recording layer, ~~and at least two layers containing 60 atomic % or more of at least one metal element, wherein one of the at least two layers contains 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47, and has a film thickness of 30 nm or more~~ a second interfacial layer, a layer having a pillar-like structure and containing not less than 30 atomic % and not more than 85 atomic % of CR, and a reflecting layer.

3. (Currently Amended) The information storage medium according to claim 2, ~~wherein said one of the at least two layers~~ the layer having the pillar-like structure contains 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than ~~28~~ 47.

4. (Currently Amended) The information storage medium according to claim 2, ~~having three of said layers containing 60 atomic % or more of at least one metal element~~ further

comprising a second protective layer stacked between the second interfacial layer and the layer having the pillar-like structure.

Claims 5-15 (Canceled)

16. (Previously Presented) The information storage medium according to claim 2, wherein the recording layer effects recording by phase change.

17. (Previously Presented) The information storage medium according to claim 2, wherein the substrate of the medium has a recording track pitch of not less than 0.3 μm and not more than 0.7 μm and has pit trains which represent at least address information at positions shifted from the track center.

Claim 18 (Canceled)

19. (Currently Amended) The information storage medium according to claim 2, wherein ~~said layer containing 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47~~ the layer having the pillar-like structure is formed at an Ar flow rate of 120 sccm or more.

20. (Previously Presented) A method of manufacturing an information storage medium which effects writing and reading by laser light, which method comprises forming a layer containing 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47 at an Ar flow rate of 120 sccm or more.

Claims 21-23 (Canceled)

24. (Currently Amended) The information storage medium according to claim 2, ~~further comprising a second interfacial layer between said recording layer and said at least two layers each containing 60 atomic % or more of at least one metal element, wherein said~~ the second interfacial layer ~~includes an~~ is comprised of oxide or a nitride.

25. (Currently Amended) The information storage medium according to claim 2, wherein ~~said~~ the first interfacial layer ~~includes an~~ is comprised of oxide or a nitride of at least one element selected from the group comprising of Cr, Ge, Si, Al, Ta, Zr, B, Hf, and Ti.